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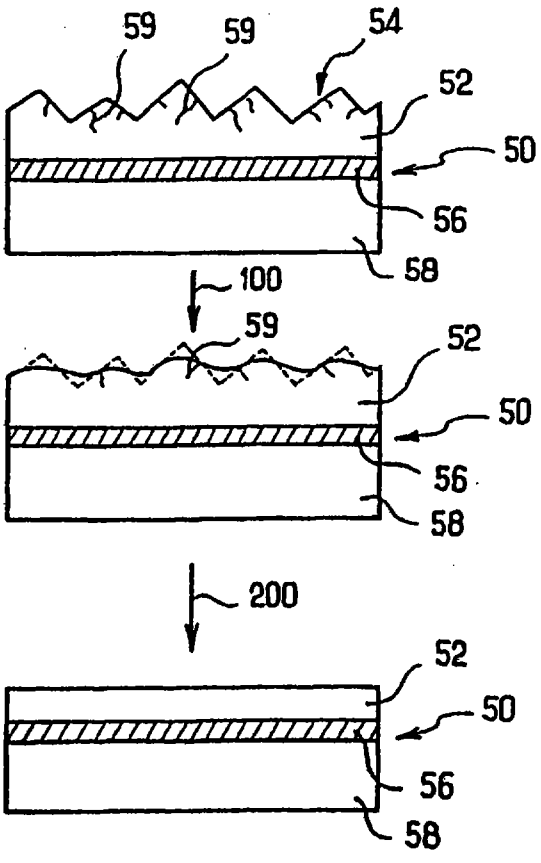
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As printed

(54) Title: METHOD FOR TREATING SUBSTRATES FOR MICROELECTRONICS AND SUBSTRATES OBTAINED ACCORDING TO SAID METHOD

(54) Titre: PROCEDE DE TRAITEMENT DE SUBSTRATS POUR LA MICRO-ELECTRONIQUE ET SUBSTRATS OBTENUS PAR CE PROCEDE



(57) Abstract: The invention relates to a method for treating substrates (50) for microelectronics or optoelectronics, whereby said substrates comprise a useful layer (52) on at least one of the surfaces thereof. The inventive method includes a mechanical/chemical polishing step occurring on a bare surface (54) of the useful layer and is characterized in that it also comprises a post-curing step in a reductive atmosphere (100) before said polishing step occurs.

(57) Abrégé: L'invention concerne un procédé de traitement de substrats (50) pour la micro-électronique ou l'opto-électronique, comportant une couche utile (52) sur au moins une de leurs faces, ce procédé comprenant une étape de polissage mécano-chimique sur la surface libre (54) de la couche utile (52), caractérisé en ce qu'il comprend en outre, une étape de recuit sous atmosphère réductrice (100), avant l'étape de polissage (200). Elle concerne également des substrats obtenus par ce procédé.

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